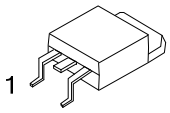
80V, 30A N-CHANNEL POWER MOSFET



TO-252

■ DESCRIPTION

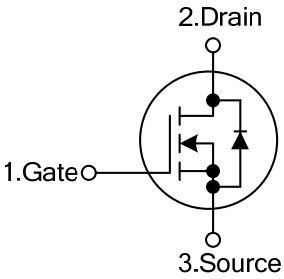
The UTC **UTT30N08** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **UTT30N08** is generally applied in high efficiency switch mode power supplies.

■ FEATURES

* $R_{DS(ON)}$＜40mΩ @ V_{GS}=10V, I_D=30A
* High Switching Speed

■ SYMBOL



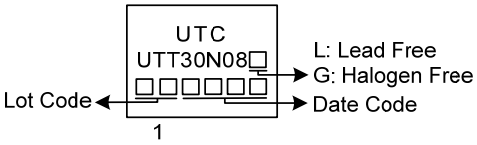
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT30N08L-TN3-R	UTT30N08G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT30N08G-TN3-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified) (Note 4)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain to Source Voltage			V_{DSS}	80	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current (Note 5)	Continuous	T_C=25°C	I_D	30	A
		T_C=100°C		18	A
	Pulsed (Note 2)		I_{DM}	90	A
Avalanche Energy	Single Pulsed (Note 3)		E_{AS}	138	mJ
Power Dissipation (T_C=25°C)			P_D	54	W
Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating; Pulse width limited by maximum junction temperature.
3. L=4mH, I_{AS}=8.3A. V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
4. Drain current limited by maximum junction temperature

■ THERMAL DATA

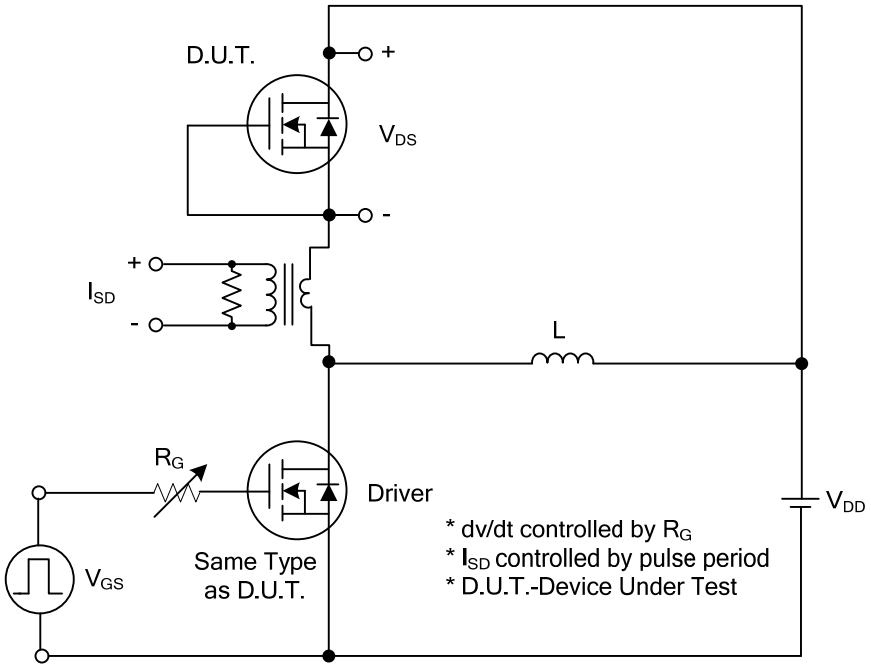
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	2.3	°C/W

■ ELECTRICAL CHARACTERISTICS

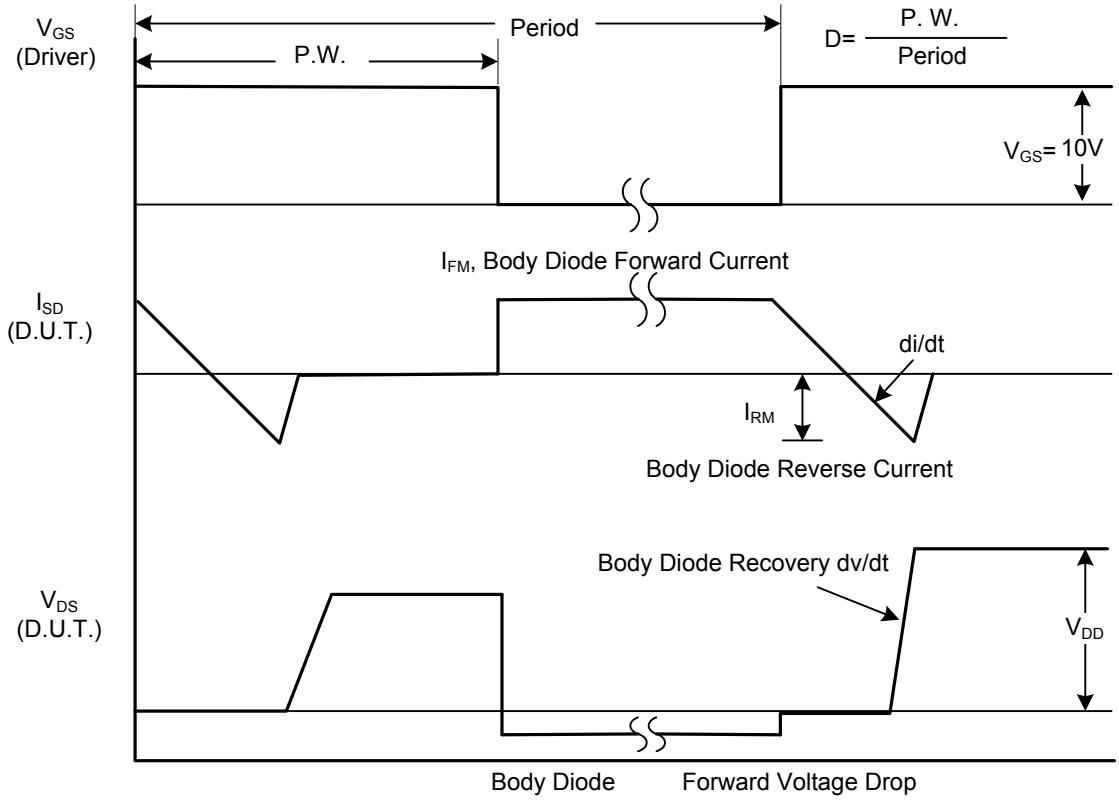
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V, T_J=150°C	80			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=80V, V_{GS}=0V,			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V , V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{GS}=V_{DS}, I_D=250μA	1.0		3.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=30A			40	mΩ
			V_{GS}=4.5V, I_D=15A			50	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{DS}=25, V_{GS}=0V, f=1.0MHz		1810		pF
Output Capacitance		C_{OSS}			160		pF
Reverse Transfer Capacitance		C_{RSS}			140		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=60V, V_{GS}=10V, I_D=30A (Note 1, 2)		61		nC
Gate to Source Charge		Q_{GS}			12		nC
Gate to Drain ("Miller") Charge		Q_{GD}			16		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=30V, I_D=15A, R_G=4.7Ω (Note 1, 2)		16		ns
Rise Time		t_R			18		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			50		ns
Fall-Time		t_F			25		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				30	A
Maximum Body-Diode Pulsed Current		I_{SM}				120	A
Drain-Source Diode Forward Voltage		V_{SD}	I_{SD}=30A, V_{GS}=0V			1.4	V

Notes: 1. Pulse Test: Pulse width≤300μs; Duty Cycle≤2%.
2. Essentially Independent of Operating Temperature Typical Characteristics

■ TEST CIRCUITS AND WAVEFORMS

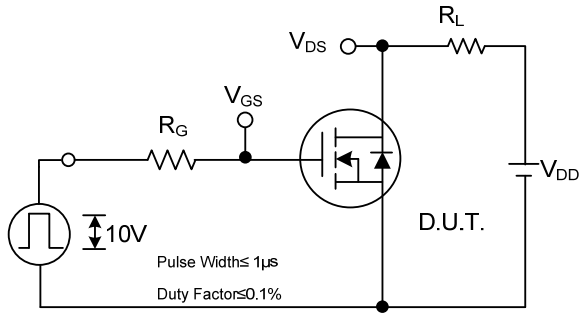


Peak Diode Recovery dv/dt Test Circuit

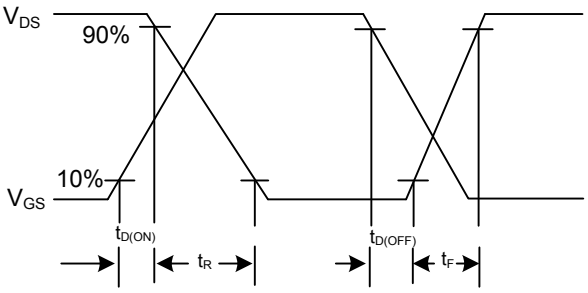


Peak Diode Recovery dv/dt Waveforms

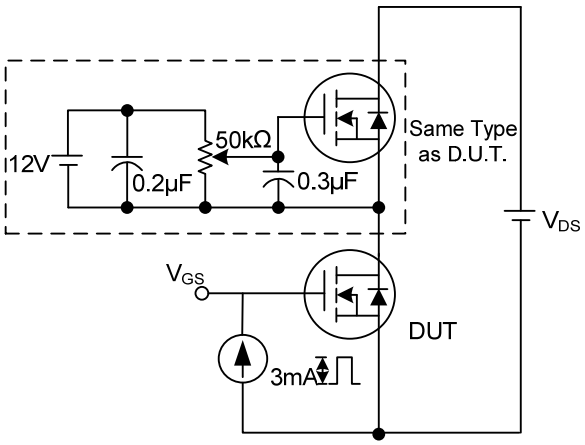
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



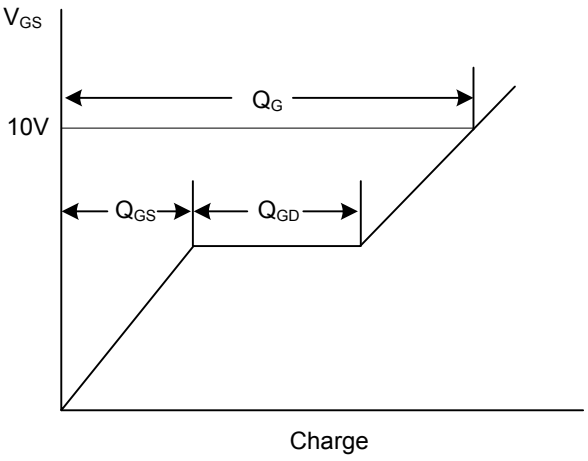
Switching Test Circuit



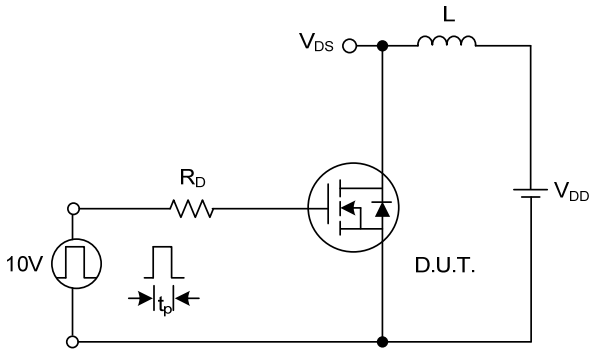
Switching Waveforms



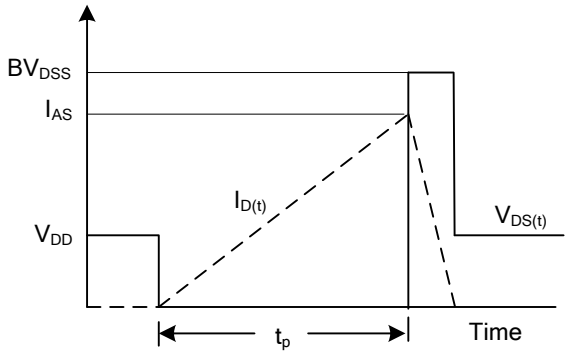
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms